Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-	-4.2	Α
Static characteristics							,
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -4.2 A; T_j = 25 °C		-	35	45	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV50EPEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV50EPEA	DQ%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-4.2	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-2.7	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-16.9	Α
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	T _{j(init)} = 25 °C; I _D = -1.3 A; DUT in avalanche (unclamped)		-	19.5	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	480	mW
			[1]	-	1.2	W
		$T_{sp} = 25 ^{\circ}C$		-	6.95	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode					,
I _S	source current	T _{amb} = 25 °C	[1]	-	-4	Α
ESD maximum	n rating					,
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

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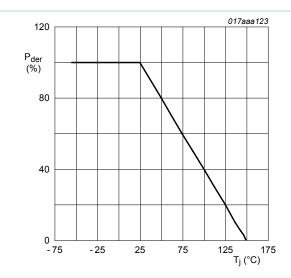


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

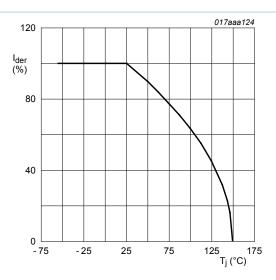


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

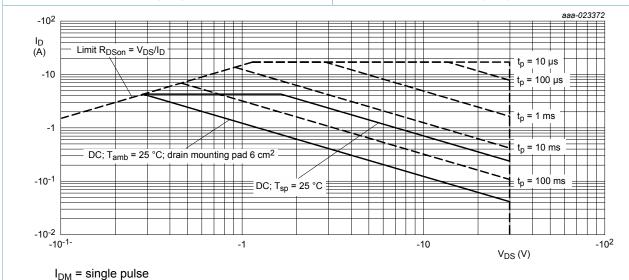


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	227	261	K/W
	from junction to ambient	1	[2]	-	91	104	K/W

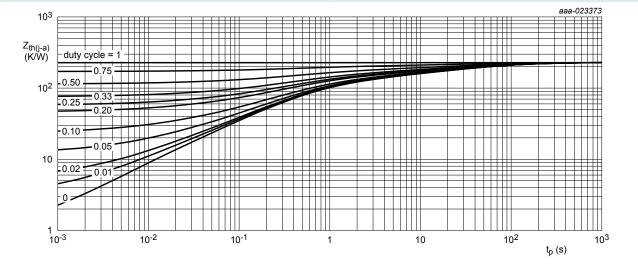
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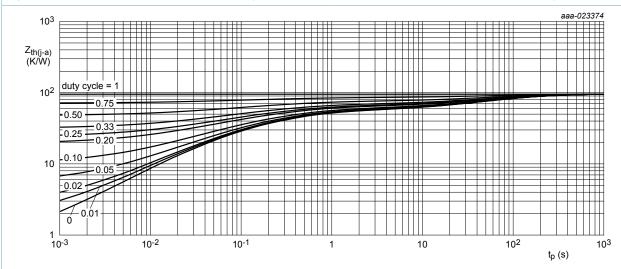
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		,			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1	-2	-3	V
I _{DSS}	drain leakage current	V _{DS} = -30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -4.2 A; T_j = 25 °C	-	35	45	mΩ
res	resistance	V_{GS} = -10 V; I_D = -4.2 A; T_j = 150 °C	-	51	67	mΩ
		V_{GS} = -4.5 V; I_D = -3.3 A; T_j = 25 °C	-	49	72	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -4.2 A; T_{j} = 25 °C	-	13.5	-	S
R_G	gate resistance	f = 1 MHz	-	13	-	Ω
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -4.2 A; V_{GS} = -10 V;	-	12.8	19.2	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	2.2	-	nC
Q_{GD}	gate-drain charge		-	2.2	-	nC
C _{iss}	input capacitance	V_{DS} = -15 V; f = 1 MHz; V_{GS} = 0 V;	-	793	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	134	-	pF
C _{rss}	reverse transfer capacitance		-	84	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -15 V; I_{D} = -4.2 A; V_{GS} = -10 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	19	-	ns
t _{d(off)}	turn-off delay time		-	36	-	ns
t _f	fall time		-	19	-	ns
Source-dra	ain diode		ı		1	
V_{SD}	source-drain voltage	I _S = -4 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.75	-1.2	V

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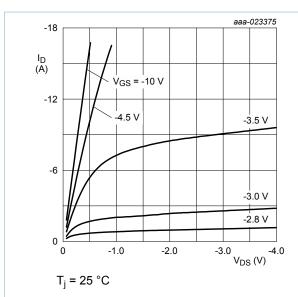


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

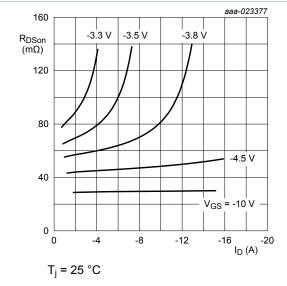


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

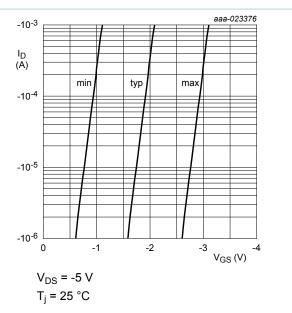


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

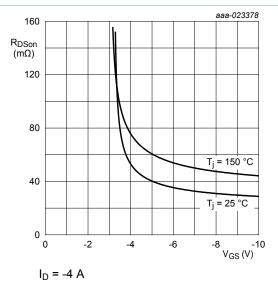


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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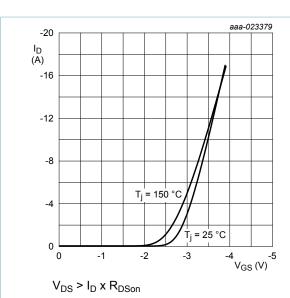


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

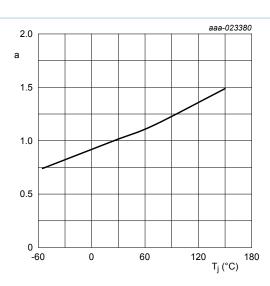


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\,^{\circ}C)}}$$

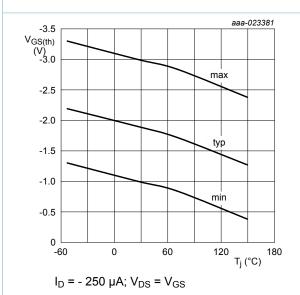


Fig. 12. Gate-source threshold voltage as a function of junction temperature

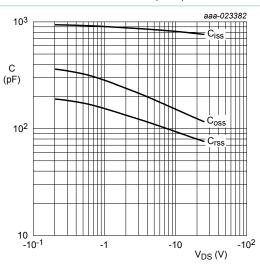


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $f = 1 MHz; V_{GS} = 0 V$

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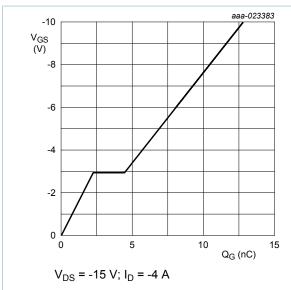


Fig. 14. Gate-source voltage as a function of gate charge; typical values

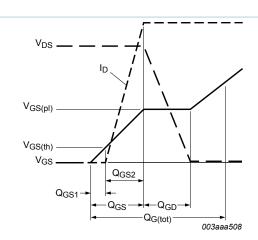


Fig. 15. Gate charge waveform definitions

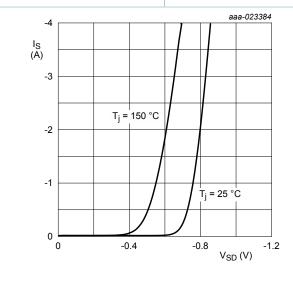
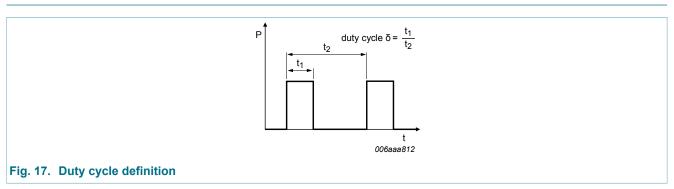


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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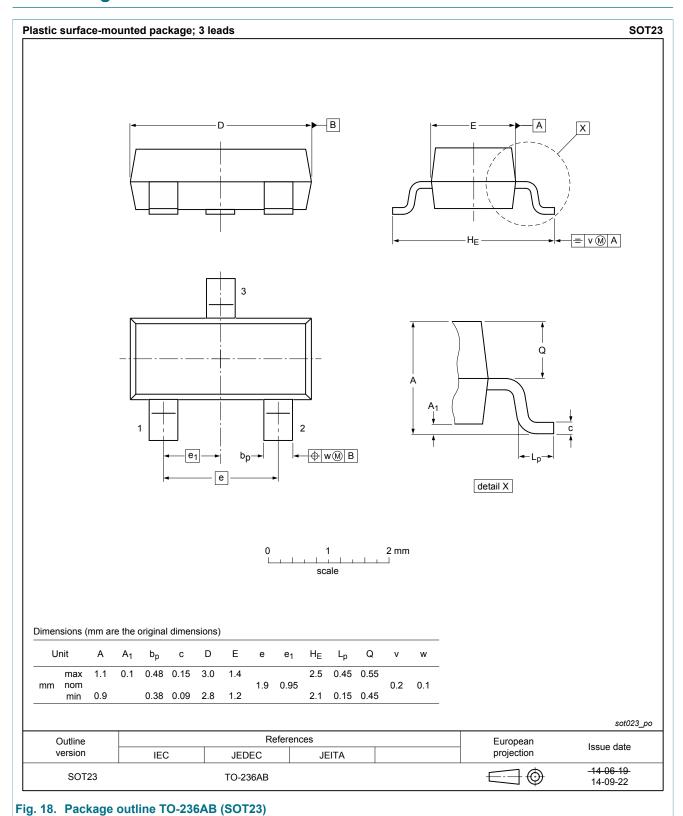
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11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

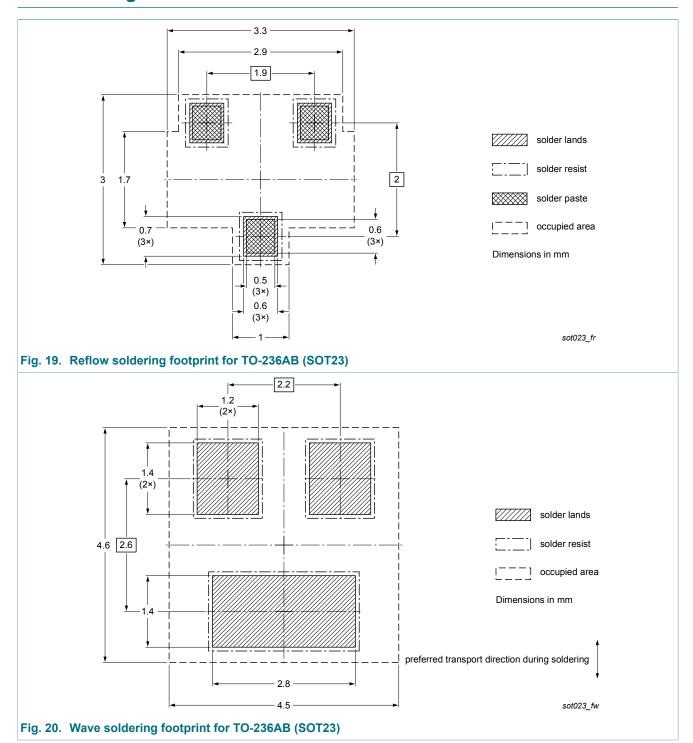
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV50EPEA v.1	20160630	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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